

L Number	Hits	Search Text	DB	Time stamp
1	103	(semiconductor or die or chip or IC) and wiring near substrate with material with ceramic	USPAT	2004/05/03 09:12
-	1	"20020158327"	USPAT;	2004/04/26 20:19
-	0	"20020158327"	US-PGPUB	
-	93	257/691 and (main or power) with electrode same (metal or copper or "Cu")	USPAT	2004/05/03 05:38
-			US-PGPUB;	2004/05/03 07:05
-	3	257/691 and (main or power) with electrode same (metal or copper or "Cu") same (multi\$4 or several) with (semiconductor or die or chip or IC)	EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	20	257/691 and (main or power) with electrode same (metal or copper or "Cu") same (multi\$4 or several or second) with (semiconductor or die or chip or IC)	USPAT;	2004/05/03 05:52
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	28	257/691 and (main or power) with electrode same (metal or copper or "Cu") same (multi\$4 or several or second or plurality) with (semiconductor or die or chip or IC)	USPAT;	2004/05/03 05:52
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	3	361/813 and (main or power) with electrode same (metal or copper or "Cu") same (multi\$4 or several or second or plurality) with (semiconductor or die or chip or IC)	USPAT;	2004/05/03 06:11
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	4	(361/813 or 361/820 or 361/775) and (main or power) with electrode same (metal or copper or "Cu") same (multi\$4 or several or second or plurality) with (semiconductor or die or chip or IC)	USPAT;	2004/05/03 06:16
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	4	(361/832 or 361/829 or 361/736) and (main or power) with electrode same (metal or copper or "Cu") same (multi\$4 or several or second or plurality) with (semiconductor or die or chip or IC)	USPAT;	2004/05/03 06:18
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	5	(361/781 or 361/783 or 361/752 or 361/753) and (main or power) with electrode same (metal or copper or "Cu") same (multi\$4 or several or second or plurality) with (semiconductor or die or chip or IC)	USPAT;	2004/05/03 06:18
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	0	5761040.pn. and (main or power) with electrode and (metal or metallic or "Ni" or nickel or copper or "Cu") with electrode	USPAT;	2004/05/03 07:06
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	1	5761040.pn. and (main or power) with electrode and (metal or metallic or "Ni" or nickel or copper or "Cu") same electrode	USPAT;	2004/05/03 07:12
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	61	257/691 and (main or power) with electrode with (metal or metallic or "Ni" or nickel or copper or "Cu")	USPAT;	2004/05/03 07:21
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	55	257/691 and (main or power) with electrode with (metal or "Ni" or nickel or copper or "Cu")	USPAT;	2004/05/03 07:21
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	
-	8	257/691 and (main or power) with electrode with material with (metal or "Ni" or nickel or copper or "Cu")	USPAT;	2004/05/03 07:22
-			US-PGPUB;	
-			EPO; JPO;	
-			DERWENT;	
-			IBM TDB	

-	610	(semiconductor or die or chip or IC) and (main) with electrode with material with (metal or "Ni" or nickel or copper or "Cu")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/03 09:11
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